



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

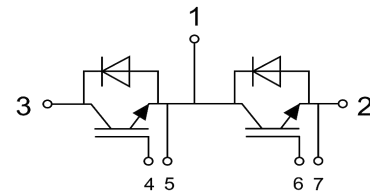
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



$V_{CES} = 600V$   
 $I_C = 200A$  at  $T_C = 80^\circ C$   
 $t_{SC} \geq 10\mu sec$   
 $V_{CE(ON)} = 1.80V$  at  $I_C = 200A$

**IGBT Half-Bridge  
POWIR 62™ Package**



**Applications:**

- Industrial Motor Drive
- Uninterruptible Power Supply
- Welding and Cutting Machine
- Switched Mode Power Supply
- Induction Heating

Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High Efficiency in a Wide Range of Applications
RBSOA Tested	Rugged Transient Performance
10μsec Short Circuit Safe Operating Area	
<b>POWIR 62™</b> Package	Industry Standard
Lead Free	RoHS Compliant, Environmental Friendly

Base Part Number	Package Type	Standard Pack	Quantity	Orderable Part Number
IRG5K200HF06B	<b>POWIR 62™</b>	Box	45	IRG5K200HF06B

**Absolute Maximum Ratings of IGBT**

$V_{CES}$	Collector to Emitter Voltage	600	V
$V_{GES}$	Continuous Gate to Emitter Voltage	±20	V
$I_C$	Continuous Collector Current	$T_C = 80^\circ C$	200 A
		$T_C = 25^\circ C$	340 A
$I_{CM}$	Pulse Collector Current	$T_J = 150^\circ C$	400 A
$P_D$	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ C, T_J = 150^\circ C$	800 W
$T_J$	Maximum IGBT Junction Temperature	150	°C
$T_{JOP}$	Maximum Operating Junction Temperature Range	-40 to +150	°C
$T_{stg}$	Storage Temperature	-40 to +125	°C

**Electrical Characteristics of IGBT at  $T_J = 25^\circ\text{C}$  (Unless Otherwise Specified)**

Parameter		Min.	Typ.	Max.	Unit	Test Conditions	
$V_{(BR)CES}$	Collector to Emitter Breakdown Voltage	600			V	$V_{GE} = 0V, I_C = 2mA$	
$V_{GE(th)}$	Gate Threshold Voltage	3.5	4.5	5.5	V	$I_C = 0.50mA, V_{CE} = V_{GE}$	
$V_{CE(ON)}$	Collector to Emitter Saturation Voltage		1.80	2.10	V	$T_J = 25^\circ\text{C}$	$I_C = 200A, V_{GE} = 15V$
			2.00		V	$T_J = 125^\circ\text{C}$	
$I_{CES}$	Collector to Emitter Leakage Current			2	mA	$V_{GE} = 0V, V_{CE} = V_{CES}$	
$I_{GES}$	Gate to Emitter Leakage Current			400	nA	$V_{GE} = \pm 20V, V_{CE} = 0$	
$R_{Gint}$	Internal Gate Resistance		1.25		$\Omega$		

**Switching Characteristics of IGBT**

Parameter		Min.	Typ.	Max.	Unit	Test Conditions	
$t_{d(on)}$	Turn-on Delay Time		220		ns	$T_J = 25^\circ\text{C}$	$V_{CC}=300V, I_C = 200A, R_G = 15\Omega, V_{GE}=\pm 15V, \text{Inductive Load}$
			210			$T_J = 125^\circ\text{C}$	
$t_r$	Rise Time		190		ns	$T_J = 25^\circ\text{C}$	
			195			$T_J = 125^\circ\text{C}$	
$t_{d(off)}$	Turn-off Delay Time		492		ns	$T_J = 25^\circ\text{C}$	
			510			$T_J = 125^\circ\text{C}$	
$t_f$	Fall Time		145		ns	$T_J = 25^\circ\text{C}$	
			140			$T_J = 125^\circ\text{C}$	
$E_{on}$	Turn-on Switching Loss		1.5		mJ	$T_J = 25^\circ\text{C}$	
			2.3			$T_J = 125^\circ\text{C}$	
$E_{off}$	Turn-off Switching Loss		8.0		mJ	$T_J = 25^\circ\text{C}$	
			8.6			$T_J = 125^\circ\text{C}$	
$Q_g$	Total Gate Charge		1100		nC	$T_J = 25^\circ\text{C}$	
$C_{ies}$	Input Capacitance		11.9		nF	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz, T_J = 25^\circ\text{C}$	
$C_{oes}$	Output Capacitance		1.15				
$C_{res}$	Reverse Transfer Capacitance		0.46				
RBSOA	Reverse Bias Safe Operating Area	Trapezoid				$I_C = 400A, V_{CC} = 480V, V_P = 600V, R_G = 15\Omega, V_{GE} = +15V \text{ to } 0V, T_J = 150^\circ\text{C}$	
SCSOA	Short Circuit Safe Operating Area	10			$\mu s$	$V_{CC} = 300V, V_{GE} = 15V, T_J = 150^\circ\text{C}$	



**Absolute Maximum Ratings of Freewheeling Diode**

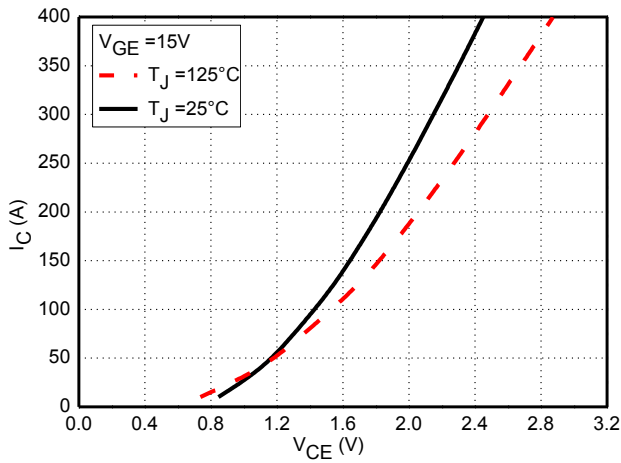
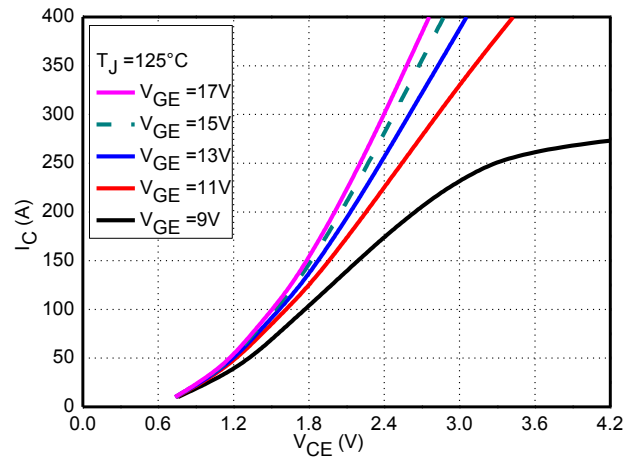
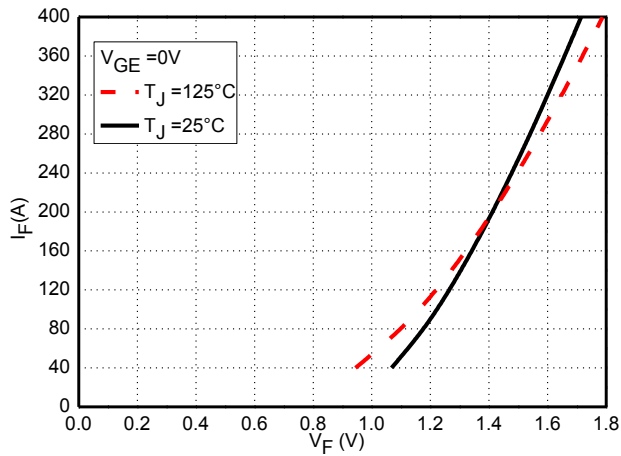
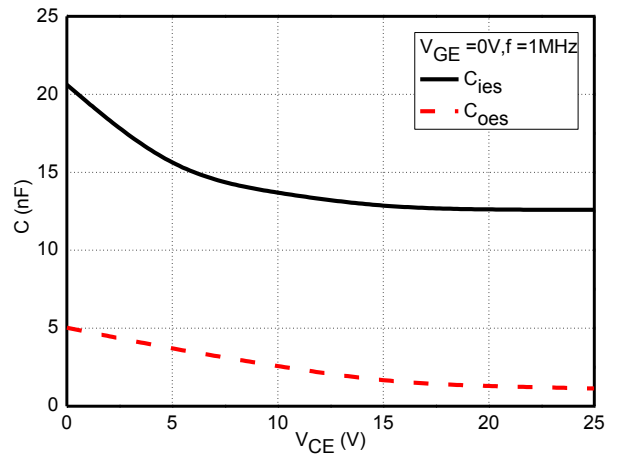
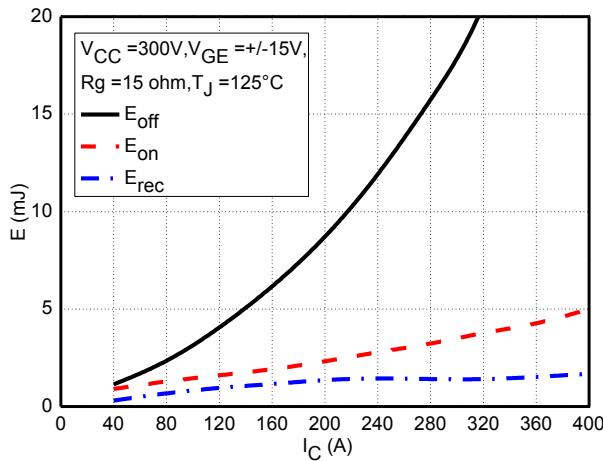
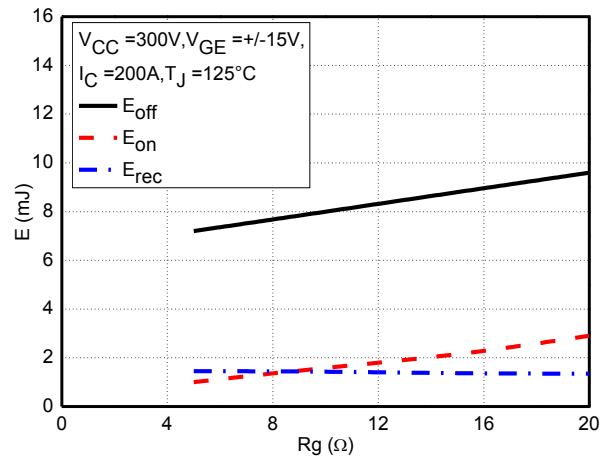
$V_{RRM}$	Repetitive Peak Reverse Voltage	600	V
$I_F$	Diode Continuous Forward Current, $T_C = 25^\circ\text{C}$	400	A
	Diode Continuous Forward Current, $T_C = 80^\circ\text{C}$	200	
$I_{FM}$	Pulse Diode Current	400	A

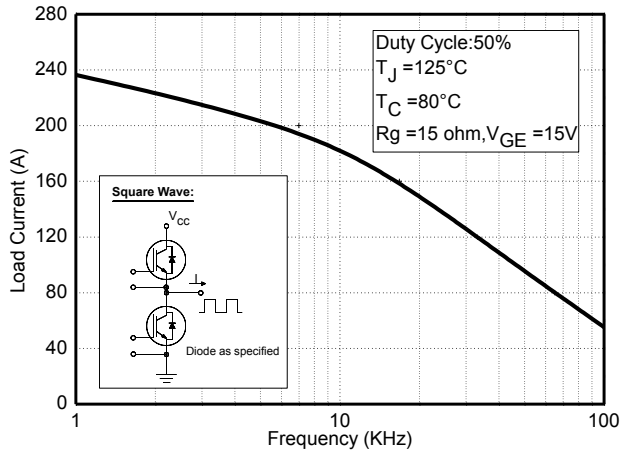
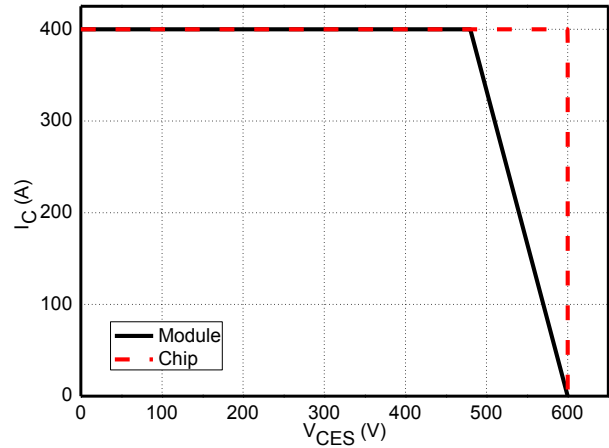
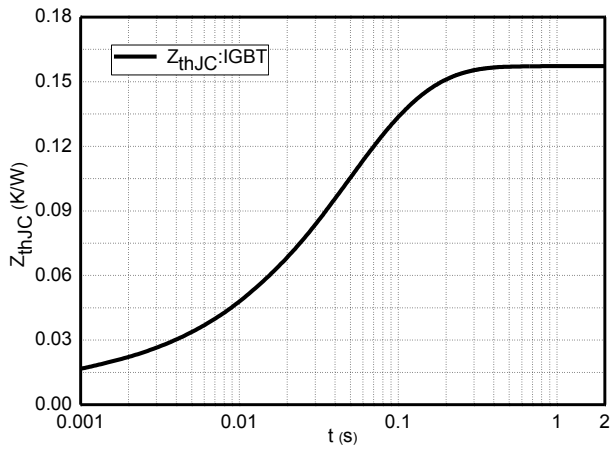
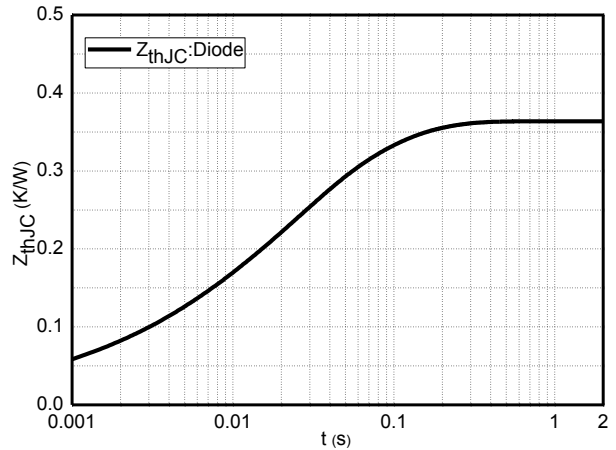
**Electrical and Switching Characteristics of Freewheeling Diode**

Parameter		Typ.	Max.	Unit	Test Conditions	
$V_F$	Forward Voltage	1.40	1.70	V	$T_J = 25^\circ\text{C}$	$I_F = 200\text{A}$ , $V_{GE} = 0\text{V}$
		1.40			$T_J = 125^\circ\text{C}$	
$I_{rr}$	Peak Reverse Recovery Current	40		A	$T_J = 25^\circ\text{C}$	$I_F = 200\text{A}$ , $di/dt = 580\text{A}/\mu\text{s}$ , $V_{rr} = 300\text{V}$ , $V_{GE} = -15\text{V}$
		55			$T_J = 125^\circ\text{C}$	
$Q_{rr}$	Reverse Recovery Charge	4.9		$\mu\text{C}$	$T_J = 25^\circ\text{C}$	
		9.4			$T_J = 125^\circ\text{C}$	
$E_{rec}$	Reverse Recovery Energy	0.4		mJ	$T_J = 25^\circ\text{C}$	
		1.2			$T_J = 125^\circ\text{C}$	

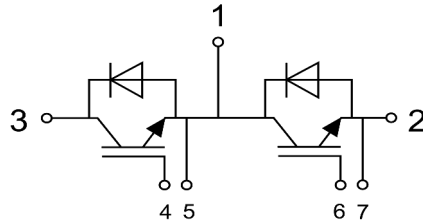
**Module Characteristics**

Parameter		Min.	Typ.	Max.	Unit
$V_{iso}$	Isolation Voltage (All Terminals Shorted), $f = 50\text{Hz}$ , 1minute			2500	V
$R_{\theta JC}$	Junction-to-Case (IGBT)		0.157		$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case (Diode)		0.363		$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Case-To-Sink (Conductive Grease Applied)		0.1		$^\circ\text{C}/\text{W}$
M	Power Terminals Screw: M6	3.0		5.0	N·m
M	Mounting Screw: M6	4.0		6.0	N·m
G	Weight		230		g


**Fig.1 Typical IGBT Saturation Characteristics**

**Fig.2 Typical IGBT Output Characteristics**

**Fig.3 Typical Freewheeling Diode Characteristics**

**Fig. 4 Typical Capacitance Characteristics**

**Fig.5 Typical Switching Loss vs. Collector Current**

**Fig.6 Typical Switching Loss vs. Gate Resistance**

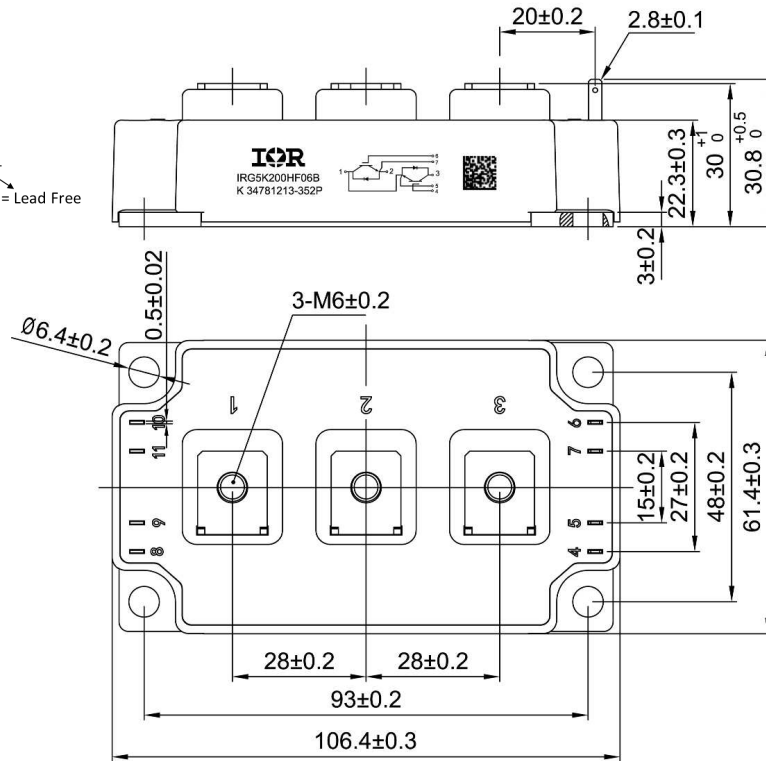

**Fig.7 Typical Load Current vs. Frequency**

**Fig.8 Reverse Bias Safe Operation Area (RBSOA)**

**Fig.9 Typical Transient Thermal Impedance (IGBT)**

**Fig.10 Typical Transient Thermal Impedance (Diode)**

**Internal Circuit:**



**Package Outline (Unit: mm):**

Marking Information  
K XXXXXXXX-YWWP  
Assembly Site Code Lot No. Date Code P = Lead Free  
Y = Year  
WW = Week



**Qualification Information<sup>†</sup>**

Qualification Level	Industrial
Moisture Sensitivity Level	Not Applicable
RoHS Compliant	Yes

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability/>